

Addendum for PCN-Datasheet 2004-018-A: BTS 5440 G

This Addendum and PCN-Datasheet refers to the PCN 2004-018-A: "Minor datasheet adaption for BTS 5240 L, BTS 5240 G, BTS 5440 G". The PCN-datasheet attached will be valid starting from August 2004.

There are the following changes in the datasheet (on page 7):

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Current limit adjustment threshold voltage	$Symbol \\ V_{CLA(T-)}$	min 2.6 -	typ - -	max - 3.6	Unit V
New:	0				,
Current limit adjustment threshold voltage	Symbol $V_{CLA(T-)}$	min 2.0	typ -	max -	Unit V
,	()	-	-	4.0	



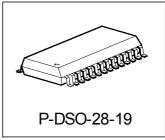
PCN 2004-018-A: BTS 5440G

Smart High-Side Power Switch Four Channels: $4 \times 25 m\Omega$ IntelliSense

Product Summary

Operating voltage	V _{bb(on)}	4,5	V	
		(Loaddur		
Active	channels	one	four parallel	
On-state resistance	R _{ON}	25	6.5	mΩ
Nominal load current	I _{L(nom)}	6.2	13.9	Α
Current limitation Low	I _{L(SCr)}		10	Α
High			40	

Package



General Description

- N channel vertical power MOSFET with charge pump, ground referenced CMOS compatible input and diagnostic feedback, monolithically integrated in Smart SIPMOS® technology.
- Providing embedded protective functions.
- Extern adjustable current limitation.

Application

- All types of resistive, inductive and capacitive loads
- μC compatible high-side power switch with diagnostic feedback for 12 V grounded loads
- Due to the adjustable current limitation best suitable for loads with high inrush currents, so as lamps
- · Replaces electromechanical relays, fuses and discrete circuits

Basic Functions

- Very low standby current
- CMOS compatible input
- Improved electromagnetic compatibility (EMC)
- · Stable behaviour at low battery voltage

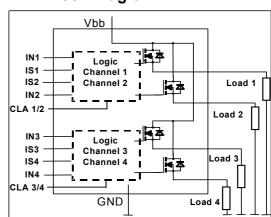
Protection Functions

- Reverse battery protection with external resistor
- Short circuit protection
- Overload protection
- Current limitation
- Thermal Shutdown
- · Overvoltage protection with external resistor
- Loss of GND and loss of V_{bb} protection
- Electrostatic discharge Protection (ESD)

Diagnostic Functions: IntelliSense

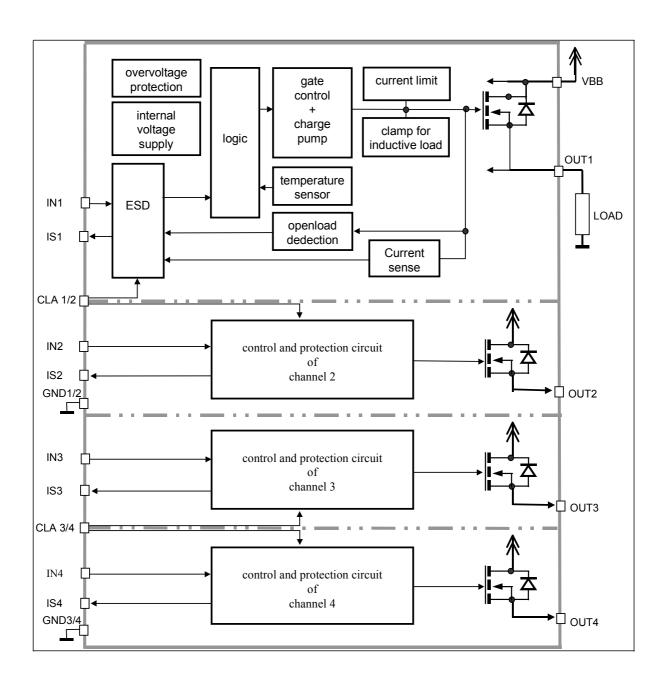
- Proportional load current sense (with defined fault signal during thermal shutdown and overload)
- Additional open load detection in OFF state
- Suppressed thermal toggling of fault signal

Block Diagram





Functional diagram





Pin definition and function

Pin	Symbol	Function
1,14,	V _{bb}	Positive power supply voltage. Design the wiring for the
15,28		simultaneous max. short circuit currents from channel 1 to 4
		and also for low thermal resistance
3	IN1	Input 1,2,3,4 activates channel 1,2,3,4 in case of logic high signal
6	IN2	
9	IN3	
12	IN4	
25,26,27	OUT1	Output 1,2,3,4 protected high-side power output of channel 1,2,3,4.
22,23,24	OUT2	Design the wiring for the max. short circuit current
19,20,21	OUT3	
16,17,18	OUT4	
4	IS1	Diagnostic feedback 14 of channel 1 to 4
5	IS2	On state: advanced current sense with defined signal in case
10	IS3	of overload or short circuit
11	IS4	Off state: High on failure
7	CLA 1/2	Current limit adjust; the current limit for channels 1/2 and 3/4 can
13	CLA 3/4	be chosen as high (potential < 2,6V) or low (potential > 3,6V).
2	GND 1/2	Ground of chip 1 (channel 1,2)
8	GND 3/4	Ground of chip 2 (channel 3,4)

Pin configuration

(top vie	w)		
V _{bb}	1 •	28	V _{bb}
GND ½	2	27	OUT1
IN1	3	26	OUT1
IS1	4	25	OUT1
IS2	5	24	OUT2
IN2	6	23	OUT2
CLA ½	7	22	OUT2
GND ¾	8	21	OUT3
IN3	9	20	OUT3
IS3	10	19	OUT3
IS4	11	18	OUT4
IN4	12	17	OUT4
CLA ¾	13	16	OUT4
V _{bb}	14	15	V_{bb}



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Maximum Ratings at T_i =25°C, unless otherwise specified

maximum Katings at 7-20 C, unless otherwise specified		,	
Parameter	Symbol	Value	Unit
Supply voltage (overvoltage protection see page 6)	$V_{\rm bb}$	28 ¹⁾	V
Supply voltage for full short circuit protection; $T_i = -40150$ °C	V _{bb(SC)}	282)	
Maximum voltage across DMOS	V_{ON}	52	
Load dump protection ³⁾ $V_{\text{LoadDump}}^{4)} = V_A + V_S$; $V_A = 13.5 \text{ V}$	$V_{Loaddump}$		
In = low or high; t_d = 400 ms; $R_1^{(4)}$ = 2 Ω			
R_{L} = 2.25 Ω		40	
R_{L} = 6.8 Ω		53	
Load current (Short - circuit current, see page 7)	I_{L}	<i>I</i> _{L(lim)} 5)	Α
Operating temperature range	T_{j}	-40+150	°C
Storage temperature range	$T_{\rm stg}$	-55+150	
Dynamical temperature rise at switching	dT	60	K
Power dissipation ⁶⁾ (DC), all channels active $T_A = 85 ^{\circ}\text{C}$	P _{tot}	1,6	W
Maximal switchable inductance, single pulse	$Z_{L(s)}$		mH
$V_{\rm bb}$ =12V, $T_{\rm jstart}$ =150°C; (see diagrams on page 12)			
$I_{L} = 6 \text{ A}, E_{AS} = 0.319 \text{ J}, R_{L} = 0 \Omega,$ one channel:		9.8	
I_L = 12 A, E_{AS} = 0.679 J, R_L = 0 Ω , two parallel channels:		5.2	
Electrostatic discharge voltage IN:	V _{ESD}	1,0	kV
(Human Body Model) IS:		2,0	
according to ANSI EOS/ESD - S5.1 - 1993 , ESD STM5.1 - 1998 OUT:		4,0	
Continuous input voltage	V_{IN}	-1016	V
Voltage at current limit adjustment pin	V _{CLA}	-1016	
Current through current limit adjustment pin	I _{CLA}	±5.0	mA
Current through input pin (DC)	I _{IN}	±5.0	
Current through sense pin (DC) (see page 11)	IIS	-5+10	

¹18...28 V for 100 hours

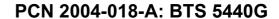
²only single pulse, R_L = 200 m Ω ; L = 8 μ H ; R and L are describing the complete circuit impedance including line, contact and generator impedances.

³Supply voltage higher than $V_{bb(AZ)}$ require an external current limit for the GND (150 Ω resistor) and sense pin.

 $^{^{4}}R_{I}$ = internal resistance of the load dump test pulse generator.

⁵Current limit is a protection function. Operation in current limitation is considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

 $^{^6}$ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6 cm2 (one layer, 70 μ m thick) copper area for V_{bb} connection. PCB is vertical without blown air.





Parameter and Conditions, each of the four channels		Symbol	Values			Unit
at T_i = -40+150 °C, V_{bb} = 916 V	, unless otherwise specified		min.	typ.	max.	
Thermal Resistance						
junction - soldering point1)	each channel:	R_{thJS}	-	-	25	K/W
junction - ambient ²⁾	one channel active:	R_{thJA}	-	40	-	K/W
	all channels active:			32		
Load Switching Capabilities	and Characteristics					
On-state resistance (V _{bb} to O	UT), (see page 13)	R _{ON}				mΩ
$T_{\rm j}$ = 25 °C, $I_{\rm L}$ = 5 A,	each channel:		-	21	25	
$T_{\rm j}$ = 150 °C,	each channel:		-	42	50	
$T_{\rm j}$ = 25 °C,	wo parallel channels:		-	11	13	
$T_{\rm j}$ = 25 °C, for	our parallel channels:		-	5.5	6.5	
Nominal load current ²⁾		I _{L(nom)}				Α
$T_{\rm a}$ = 85°C, $T_{\rm j} \le 150$ °C,	one channel active:	, ,	5.7	6.2	-	
two channels	active, per channel:		4.0	4.4	-	
four channels	active, per channel:		3.1	3.4	-	
Output voltage drop limitation	at small load currents	V _{ON(NL)}	-	40	-	mV
$I_{L} = 0.5 \text{ A}$,				
Output current while GND dis	connected ³⁾	/ _{L(GNDhigh)}	-	-	2	mA
(see diagram page 12)						
$V_{IN} = 0 \text{ V}$						

¹Soldering point is measured at Vbb-pin

 $^{^2\}text{Device}$ on 50mm*50mm*1.5mm epoxy PCB FR4 with 6 cm2 (one layer, 70µm thick) copper area for V_{bb} connection. PCB is vertical without blown air.

 $^{^{3}}$ not subject to production test, specified by design





Parameter and Conditions, each of the four channels	Symbol		Values		Unit
at T_i = -40+150 °C, V_{bb} = 916 V, unless otherwise specified		min.	typ.	max.	
Load Switching Capabilities and Characteristics	•	•	•	•	
Turn-on time ¹⁾ to 90% V_{OUT}	<i>t</i> on	-	90	200	μs
$R_{L} = 12 \Omega, V_{bb} = 12 V$					
Turn-off time ¹⁾ to 10% V _{OUT}	$t_{\rm off}$	-	100	220	
$R_{L} = 12 \Omega, V_{bb} = 12 V$					
Slew rate on ¹⁾ 10 to 30% V _{OUT} ,	dV/dt _{on}	0.1	0.25	0.45	V/µs
$R_{L} = 12 \Omega, V_{bb} = 12 V$					
Slew rate off ¹⁾ 70 to 40% V _{OUT} ,	-dV/dt _{off}	0.09	0.25	0.4	
$R_{L} = 12 \Omega, V_{bb} = 12 V$					

Operating Parameters

Operating voltage ²⁾	V _{bb(on)}	4.5	ı	28	V
Overvoltage protection ³⁾	$V_{\rm bb(AZ)}$	41	47	52	
$I_{\rm bb}$ = 40 mA					
Standby current ⁴⁾	I _{bb(off)}				μA
(see diagram on page 13)					
$T_{\rm j}$ = -40+25 °C, $V_{\rm IN}$ = 0 V		-	10	15	
<i>T</i> _j = 150 °C		_	-	40	

¹See timing diagram on page 14.

^{2&}lt;sub>18</sub>V...28V for 100 hours

 $^{^3}$ Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the status pin and GND pin (e.g. 150 Ω). See also $V_{Out(CL)}$ in table of protection functions and circuit diagram on page 11.

⁴Measured with load; for the whole device; all channels off.



	<u> </u>	1	_			
Parameter and Conditio	ns, each of the four channels	Symbol		Values	,	Unit
at $T_j = -40+150$ °C, $V_{bb} = 9$	16 V, unless otherwise specified		min.	typ.	max.	
Operating Parameters						
Off-State output current (i	ncluded in I _{bb(off)})	I _{L(off)}	-	1.5	8	μΑ
V_{IN} = 0 V, each channel						
Operating current ¹⁾		I _{GND}	-	1.6	4	mA
V_{IN} = 5 V, per active chan	nel					
Protection Functions ²⁾						
Current limit, (see timing dia	agrams, page 15)	/ _{L(LIM)}				Α
Low level; if potential at	: CLA = high		7	11	14	
High level; if potential a	t CLA = low		40	50	60	
Current limit adjustment th	nreshold voltage	V _{CLA(T-)}	2.0	-	-	V
		V _{CLA(T+)}	-	-	4.0	
Repetitive short circuit cui	rrent limit	I _{L(SCr)}				Α
$T_j = T_{jt}$ (see timing diagrams	s on page 15)					
High level	one active channel:		-	40	-	
	two active channels ³⁾ :		-	40	-	
Low level	one active channel:		_	7	-	
	two active channels ³⁾ :		_	7	-	
Initial short circuit shutdov	vn time low level:	t _{off(SC)}	-	3.5	-	ms
$T_{\rm j,start} = 25^{\circ} \rm C$; $V_{\rm bb} = 13.5$	V high level:	, ,	-	0.75	-	
Output clamp (inductive lo	pad switch off) ⁴⁾	V _{Out(CL)}	-	-15	-	V
$I_{L} = 40 \text{ mA}$						
Thermal overload trip tem	perature	T_{it}	150	170	-	°C
Thermal hysteresis		$\Delta T_{\rm jt}$	-	10	-	K

 $^{^{1}}$ Add $I_{|S}$, if $I_{|S} > 0$

²Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

³At the beginning of the short circuit the double current is possible for a short time.

 $^{^4}$ If channels are connected in parallel, output clamp is usually accomplished by the channel with the lowest $V_{Out(CL)}$.



Parameter and Conditions, each of the four channels	Symbol		Values		Unit
at T_j = -40+150 °C, V_{bb} = 916 V, unless otherwise specified		min.	typ.	max.	
Diagnostic Characteristics					
Open load detection voltage	V _{OUT(OL)}	2	3.2	4.4	V
Internal output pull down ¹⁾	R _{OUT(PD)}	11	23	35	kΩ
V _{OUT} = 13.5 V					
Current sense ratio, static on-condition	k _{ILIS}				
$k_{ILIS} = I_{L} : I_{IS}$					
$I_{L} = 0.5 \text{ A}$		4640	5800	6960	
$I_{L} = 3 \text{ A}$		4900	5400	5900	
$I_{L} = 6 \; A$		4900	5350	5800	
Sense signal in case of fault-conditions ²⁾	V _{fault}	5	6.2	7.5	V
in off-state					
Current saturation of sense fault signal	I _{fault}	4	-	-	mA
Sense signal delay after thermal shutdown ³⁾	t _{delay(fault)}	-	-	1.2	ms
Current sense output voltage limitation	V _{IS(lim)}	5.4	6.5	7.3	V
$I_{1S} = 0$, $I_{L} = 5$ A					
Current sense leakage/offset current	I _{IS(LH)}	-	-	5	μΑ
$V_{IN} = 5 \text{ V}, I_{L} = 0, V_{IS} = 0$					
Current sense settling time to I_{IS} static ±10%	$t_{son(IS)}$	-	-	400	μs
after positive input slope ⁴⁾ , $I_L = 0$ to 5A					
Current sense settling time to I_{IS} static ±10%	$t_{\sf slc(IS)}$	-	_	300	
after change of load current ⁴⁾ , $I_{L} = 2.5$ to 5A					

¹In case of floating output, the status doesn't show open load.

 $^{^2}$ Fault condition means output voltage exceeds open load detection voltage $V_{\mbox{OUT}(\mbox{OL})}$

³In the case of thermal shutdown the V_{fault} signal remains for $t_{\text{delay(fault)}}$ longer than the restart of the switch (see diagram on page 16).

 $^{^{4}}$ not subject to production test, specified by design



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Parameter	Symbol	Values			Unit
at T_i = -40+150 °C, V_{bb} = 916 V, unless otherwise specif	fied	min.	typ.	max.	
Diagnostic Characteristics	•			•	•
Status invalid after negative input slope	t _{d(SToff)}	-	-	1.2	ms
Status invalid after positive input slope	$t_{d(STOL)}$	-	-	20	μs
with open load	, , ,				
Input Feedback ¹⁾					
Input resistance (see circuit page 11)	R _I	2.0	3.5	5.5	kΩ
Input turn-on threshold voltage	V _{IN(T+)}	-	-	2.4	V
Input turn-off threshold voltage	$V_{\rm IN(T-)}$	1.0	-	-	
Input threshold hysteresis	$\Delta V_{IN(T)}$	-	0.5	-	
Off state input current	I _{IN(off)}	3	-	40	μA
$V_{IN} = 0.4 \; V$]
On state input current	I _{IN(on)}	20	50	90	
<i>V</i> _{IN} = 5 V					
Reverse Battery ²⁾			_	_	
Reverse battery voltage	-V _{bb}	-	-	27	V
Drain-source diode voltage ($V_{OUT} > V_{bb}$)	-V _{ON}	-	330		mV
$T_{\rm j}$ = 150 °C, $I_{\rm bb}$ = -10 mA					

 $^{^{1}}$ If ground resistors R_{GND} are used, add the voltage drop across these resistor.

 $^{^2}$ Requires a 150 Ω resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Power dissipation is higher compared to normal operating conditions due to the voltage drop across the drain-source diode. The temperature protection is not active during reverse current operation! Input and status currents have to be limited. (see max. ratings page 4)



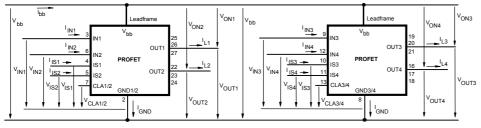
Truth Table - for each of the four channels

	Input	Output	Diagnostic
	level	level	output
Normal	L	L	Z ¹⁾
Operation	Н	V_{bb}	$I_{\rm IS} = I_{\rm L} / {\rm kilis}$
Current Limitation ²⁾	Н	$V_{ m bb}$	V _{fault}
Short circuit	L	L	Z ¹⁾
to GND	Н	L	V _{fault}
Overtemperature	L	L	Z ¹⁾
	Н	L	V _{fault}
Short circuit	L	$V_{ m bb}$	V _{fault}
to V _{bb}	Н	$V_{ m bb}$	$< I_{\rm IS} = I_{\rm L} / {\rm kilis}^{3)}$
Open load	L	>V _{out(OL)}	V_{fault}
	Н	$V_{ m bb}$	Z ¹⁾

L = "Low" Level Z = high impedance, potential depends on external circuit
H = "High" Level V_{fault} = 5V typ., constant voltage independent of external sense resistor.

Parallel switching of channels is possible by connecting the inputs and outputs parallel. The current sense ouputs have to be connected with a single sense resistor.

Terms

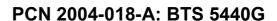


Leadframe (V_{bb}) is connected to pin 1, 14, 15, 28

¹L-potential by using a sense resistor

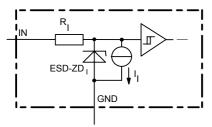
²Current limitation is only possible while the device is switched on.

 $^{^3}$ Low ohmic short to V_{bb} may reduce the output current I_L and therefore also the sense current I_{lS} .





Input circuit (ESD protection), IN1...IN4

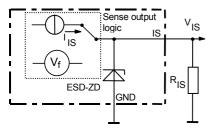


The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

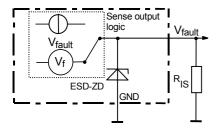
Sense-Status output, IS1...IS4

ON-State: Normal operation: $I_S = I_L / kILIS$

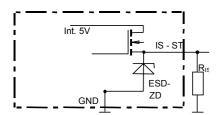
$$V_{\text{IS}} = I_{\text{S}} * R_{\text{IS}};$$
 $R_{\text{IS}} = 1 \text{k}\Omega \text{ nominal}$
 $R_{\text{IS}} > 500\Omega$



ESD zener diode: $V_{\rm ESD}$ = 6,1 V typ., max. 14 mA; ON-State: Fault condition so as thermal shut down or current limitation

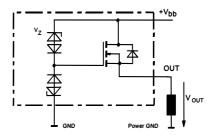


 $V_{\rm fault}$ = 6 V typ ; $V_{\rm fault}$ < $V_{\rm ESD}$ under all conditions OFF-State diagnostic condition: Open Load, if $V_{\rm OUT}$ > 3 V typ.; IN low



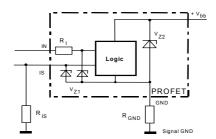
ESD-Zener diode: 6,1V typ., max. 5mA; $R_{\rm ST(ON)}$ < 375 Ω at 1,6mA.. The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

Inductive and overvoltage output clamp, OUT1...OUT4



 V_{Out} clamped to $V_{\text{Out}(\text{CL})}$ = -15 V typ.

Overvolt. Protection of logic part OUT1...OUT4

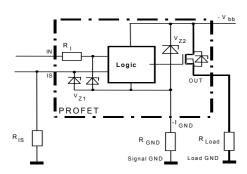


$$\begin{split} V_{Z1} &= 6,1 \text{V typ., } V_{Z2} = 47 \text{V typ., } R_{GND} = 150 \Omega \text{ ,} \\ R_{\text{IS}} &= 1 \text{k} \Omega \text{ , } R_{\text{I}} = 3,5 \text{k} \Omega \text{ typ.} \end{split}$$



Reverse battery protection

OUT1...OUT4

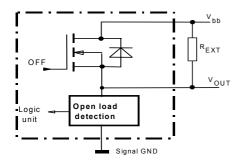


$$V_{Z1}$$
 = 6,1V typ., V_{Z2} = 47V typ., R_{GND} = 150 Ω
 R_{IS} = 1k Ω , R_{I} = 3,5k Ω typ.

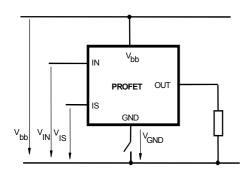
In case of reverse battery the load current has to be limited by the load. Protection functions are not active.

Open load detection, OUT1...OUT4

Off-state diagnostic condition: Open load, if $V_{OUT} > 3 \text{ V typ.}$; IN = low

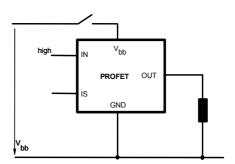


GND disconnect



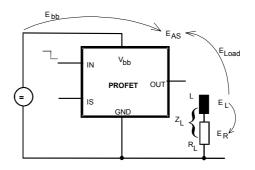
Any kind of load.

Vbb disconnect with energized inductive load



For inductive load currents up to the limits defined by Z_L each switch is protected against loss of V_{bb} . (max. ratings and diagram on page 12) Consider at your PCB layout that in the case of Vbb disconnection with energized inductive load all the load current flows through the GND connection.

Inductive load switch-off energy dissipation



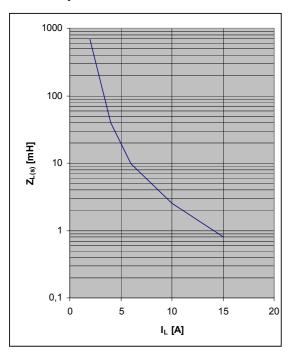
Energy stored in load inductance: $E_L = \frac{1}{2} * L * I_L^2$ While demagnetizing load inductance, the energy dissipated in PROFET is $E_{AS} = E_{bb} + E_L - E_R = V_{ON(CL)} * i_L(t) dt$, with an approximate solution for $R_L > 0\Omega$:

$$E_{AS} = \frac{I_L * L}{2 * R_L} * (V_{bb} + |V_{OUT(CL)|}) * \ln(1 + \frac{I_L * R_L}{|V_{OUT(CL)|}})$$



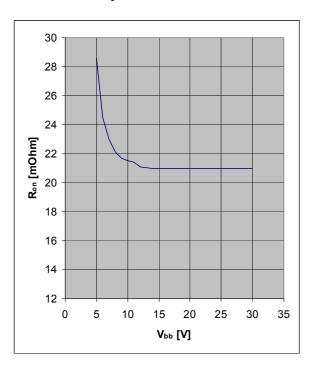
Maximum allowable load inductance for a single switch off (one channel)

L =f(IL);
$$T_{\text{jstart}} = 150^{\circ}\text{C}$$
, $V_{\text{bb}} = 12\text{V}$, $R_{\text{L}} = 0\Omega$



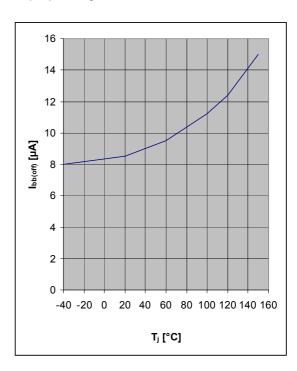
Typ. on-state resistance

$$R_{ON} = f(V_{bb}, T_j); I_L = 5 \text{ A} ; V_{in} = \text{high}$$



Typ. standby current

$$I_{bb(off)} = f(T_j)$$
; $V_{bb} = 16 \text{ V}$; $V_{IN1...4} = \text{low}$

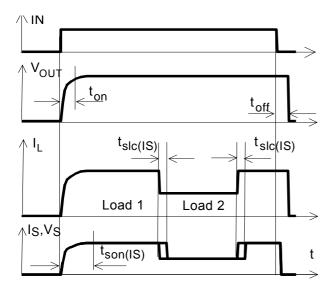




Timing diagrams

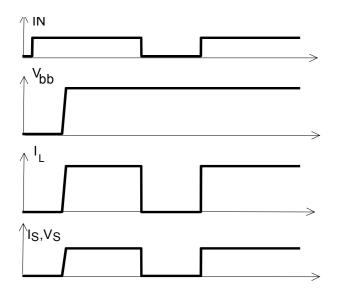
All channels are symmetric and consequently the diagrams are valid for channel 1 to channel 4.

Figure 1a: Switching a resistive load, change of load current in on-condition



The sense signal is not valid during settling time after turn on or change of load current. $tslc(IS) = 300 \mu s typ$.

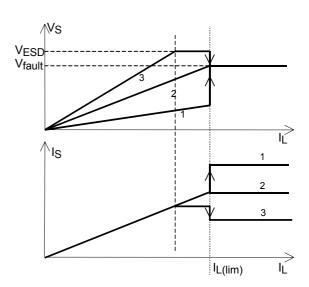
Figure 1b: V_{bb} turn on



proper turn on under all conditions

Figure 1c: Behaviour of sense output: Sense current (I_S) and sense voltage (V_S) as function of load current dependent on the sense resistor.

Shown is $V_{\rm S}$ and $I_{\rm S}$ for three different sense resistors. Curve 1 refers to a low resistor, curve 2 to a medium-sized resistor and curve 3 to a big resistor. Note, that the sense resistor may not falls short of a minimum value of 500Ω .



$$I_{\rm S} = I_{\rm L} / k_{\rm ILIS}$$

 $V_{\rm IS} = I_{\rm S} * R_{\rm IS}; R_{\rm IS} = 1 {\rm k}\Omega$ nominal
 $R_{\rm IS} > 500\Omega$



Figure 2a: Switching a lamp

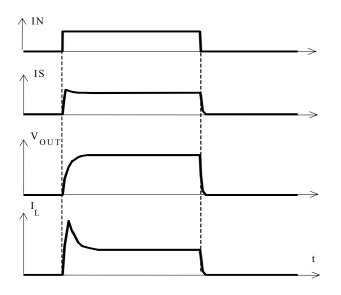


Figure 2b: Switching a lamp with current limit: The behaviour of I_S and V_S is shown for a resistor, which refers to curve 1 in figure 1c

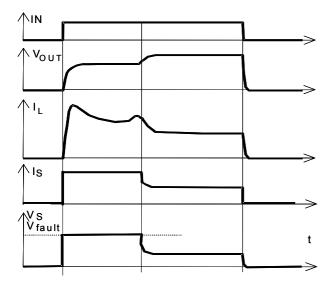
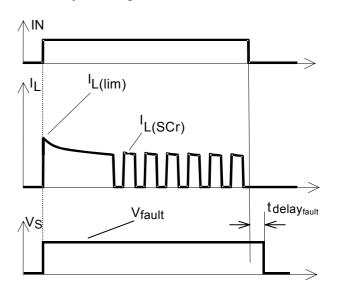
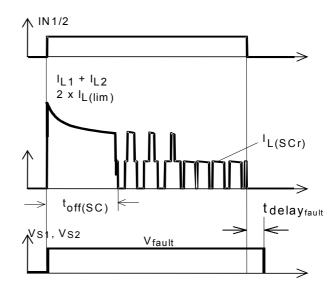


Figure 3a: Short circuit: Shut down by overtemperature, reset by cooling



Heating up may require several milliseconds, depending on external conditions. $I_{L(lim)}$ = 50A typ. increases with decreasing temperature.

Figure 3a: Turn on into short circuit, shut down by overtemperature, restart by cooling (channel 1 and 2 switched parallel)



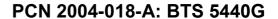




Figure 4a: Overtemperature

Reset if $T_i < T_{it}$

The behaviour of I_{S} and V_{S} is shown for a resistor, which refers to curve 1 in figure 1c.

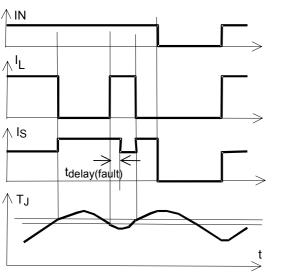
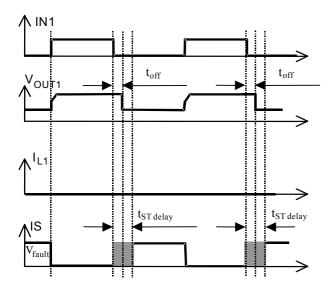
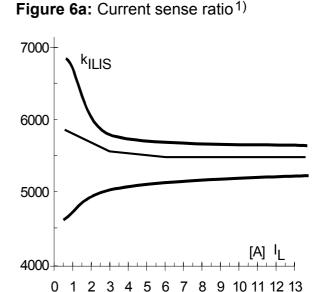


Figure 5a:Open-load: detection in OFF-state, turn on/off to open load.

Open load of channel 1; other channels normal opertaion.



 $t_{\rm Off}$ = 250µs max.; $t_{\rm ST\ delay}$ = 500µs max. with pull up resistor at output



¹This range for the current sense ratio refers to all devices. The accuracy of the k_{ILIS} can be raised by calibrating the value of k_{ILIS} for every single device.

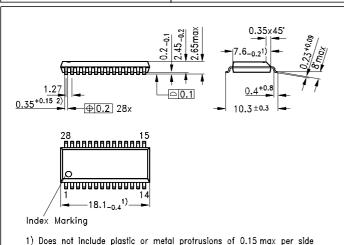


Package and ordering code

all dimensions in mm

P-DSO-28-19

Sales Code	BTS 5440G
Ordering Code	Q67060-S6136



2) Does not include dambar protrusion of 0.05 max per side

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